**Product data sheet** 

## 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 2. Features and benefits

- Trench MOSFET technology
- · Low threshold voltage
- · Enhanced power dissipation capability of 940 mW
- ElectroStatic Discharge (ESD) protection > 2KV HBM
- AEC-Q101 qualified

## 3. Applications

- LED driver
- · Power management
- Low-side loadswitch
- · Switching circuits

### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	20	V
$V_{GS}$	gate-source voltage	T <sub>j</sub> = 25 °C; T <sub>amb</sub> = 25 °C		-8	-	8	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	-	2.8	Α
Static characte	Static characteristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 4.5 V; $I_D$ = 2.8 A; $T_j$ = 25 °C		-	63	73	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.



# 5. Pinning information

### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	3	D -
2	S	source		
3	D	drain	1 2 TO-236AB (SOT23)	G S 017aaa255

# **6. Ordering information**

### **Table 3. Ordering information**

Type number	Package	Package					
	Name	Description	Version				
PMV65UNEA	TO-236AB	plastic surface-mounted package; 3 leads	SOT23				

# 7. Marking

### **Table 4. Marking codes**

Type number	Marking code[1]
PMV65UNEA	EM%

[1] % = placeholder for manufacturing site code

# 8. Limiting values

#### **Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	20	V
$V_{GS}$	gate-source voltage	T <sub>j</sub> = 25 °C; T <sub>amb</sub> = 25 °C		-8	8	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	2.8	Α
		V <sub>GS</sub> = 4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	1.8	Α
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$		-	11	Α
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$T_{j(init)}$ = 25 °C; $I_D$ = 0.3 A; DUT in avalanche (unclamped)		-	5.6	mJ
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	490	mW
			[1]	-	940	mW
		T <sub>sp</sub> = 25 °C		-	6.25	W
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-drain d	iode					
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	0.9	Α
ESD Maximum	rating					
V <sub>ESD</sub>	electrostatic discharge voltage	НВМ		-	2000	V

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

<sup>[2]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

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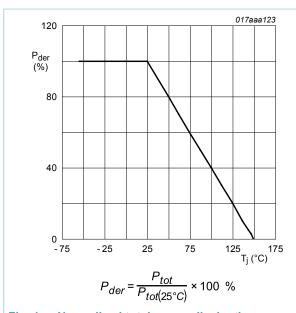


Fig. 1. Normalized total power dissipation as a function of junction temperature

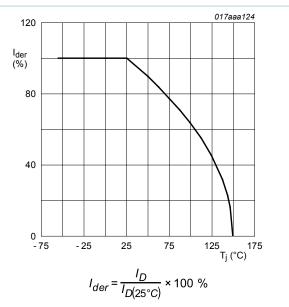
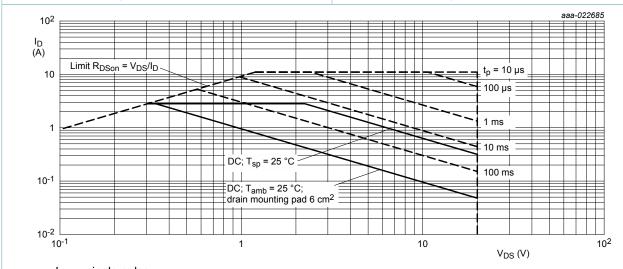


Fig. 2. Normalized continuous drain current as a function of junction temperature



I<sub>DM</sub> = single pulse

Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	-	[1]	-	221	254	K/W
			[2]	_	116	133	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	17	20	K/W

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- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

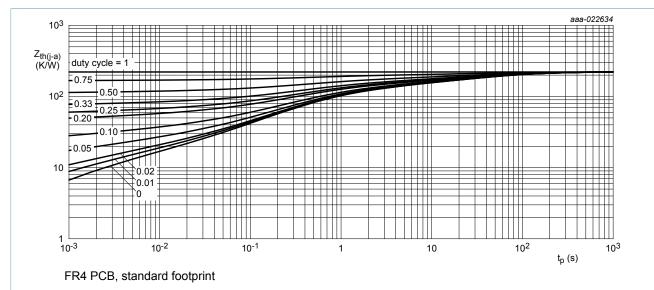


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

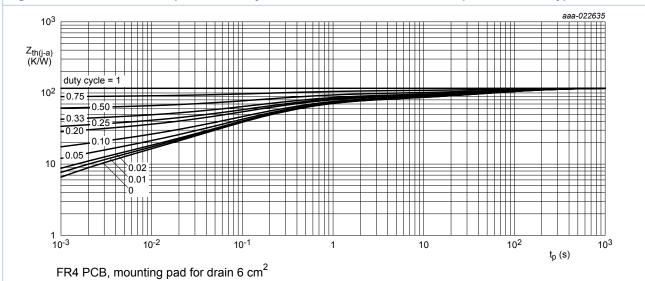


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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### 10. Characteristics

#### Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	20	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = 250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$	0.45	0.7	1	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 20 V; V <sub>GS</sub> = 0 V	-	-	1	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	10	μΑ
		$V_{GS} = -8 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	-10	μΑ
		V <sub>GS</sub> = 4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	5	μΑ
		V <sub>GS</sub> = -4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-5	μΑ
DOON	drain-source on-state	$V_{GS}$ = 4.5 V; $I_D$ = 2.8 A; $T_j$ = 25 °C	-	63	73	mΩ
	resistance	$V_{GS}$ = 4.5 V; $I_D$ = 2.8 A; $T_j$ = 150 °C	-	93	108	mΩ
		$V_{GS}$ = 2.5 V; $I_D$ = 2.4 A; $T_j$ = 25 °C	-	71	83	mΩ
		$V_{GS}$ = 1.8 V; $I_D$ = 0.8 A; $T_j$ = 25 °C	-	83	94	mΩ
g <sub>fs</sub>	forward transconductance	$V_{DS}$ = 10 V; $I_{D}$ = 3 A; $T_{j}$ = 25 °C	-	11	-	S
R <sub>G</sub>	gate resistance	T <sub>j</sub> = 25 °C; f = 1 MHz	-	1.8	-	Ω
Dynamic ch	aracteristics					
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 2.8 A; V <sub>GS</sub> = 4.5 V;	-	3.8	6	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	0.3	-	nC
Q <sub>GD</sub>	gate-drain charge		-	0.9	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 10 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	291	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	52	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	43	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 10 V; $I_{D}$ = 2.8 A; $V_{GS}$ = 4.5 V;	-	8	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	23	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	35	-	ns
t <sub>f</sub>	fall time	1	-	12	-	ns
Source-drai	n diode			1	1	
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 0.9 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.7	1.2	V
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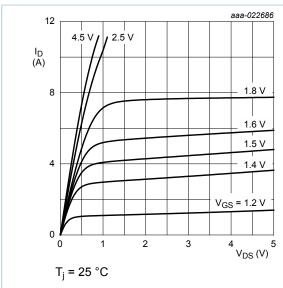


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

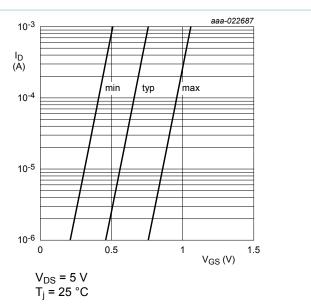


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

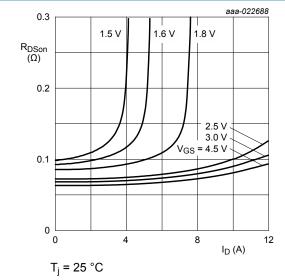


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

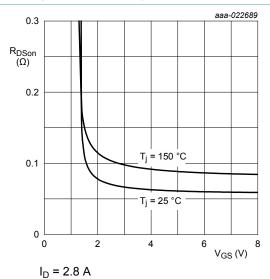


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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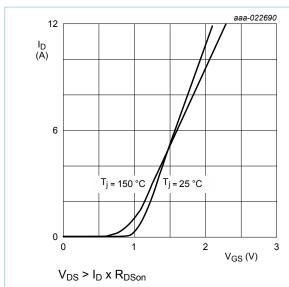


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

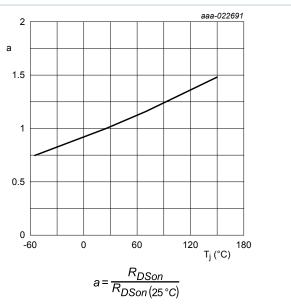


Fig. 11. Normalized drain-source on-state resistance as a function of ambient temperature; typical values

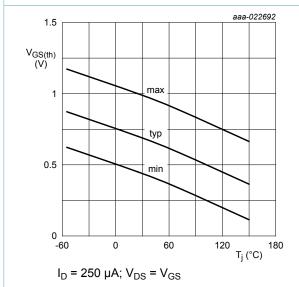


Fig. 12. Gate-source threshold voltage as a function of ambient temperature

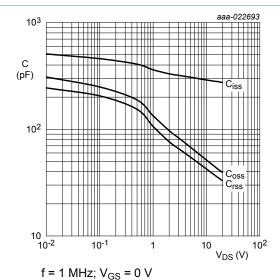


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

#### 20 V, N-channel Trench MOSFET

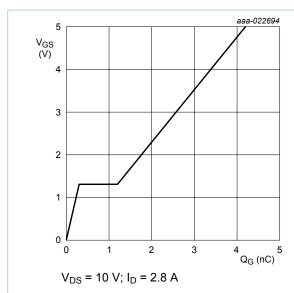


Fig. 14. Gate-source voltage as a function of gate charge; typical values

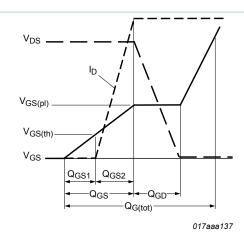


Fig. 15. Gate charge waveform definitions

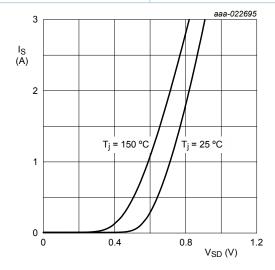
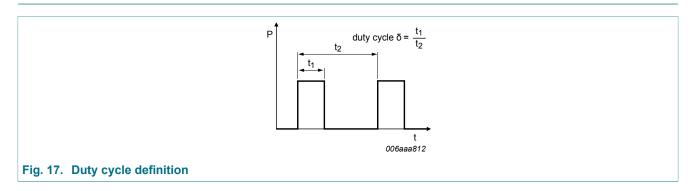


Fig. 16. Source current as a function of source-drain voltage; typical values

 $V_{GS} = 0 V$ 

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# 11. Test information

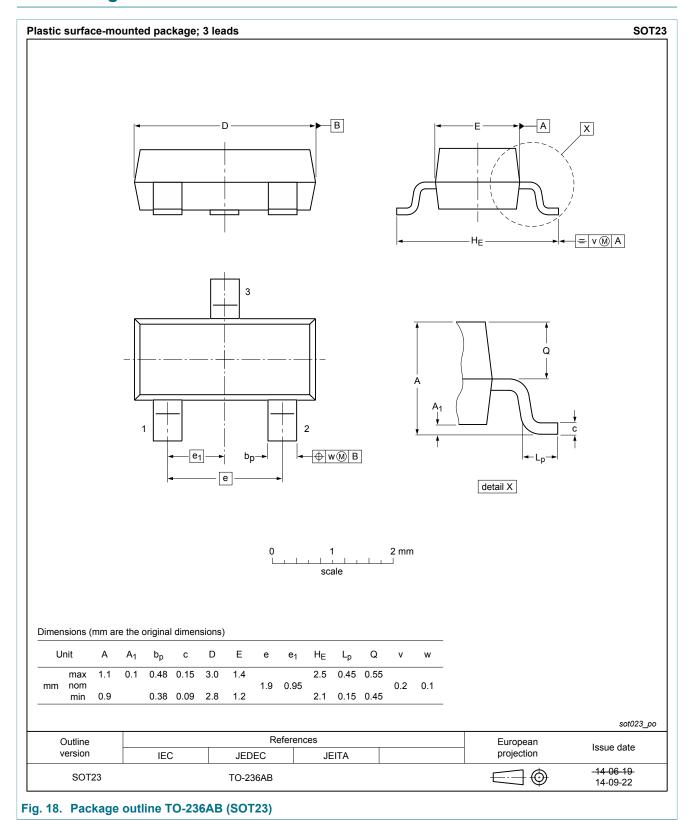


## **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

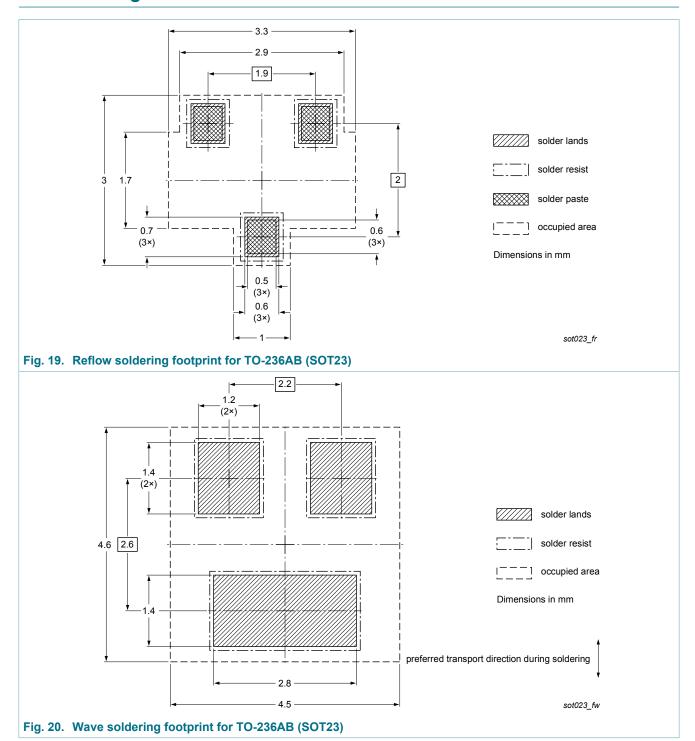
20 V, N-channel Trench MOSFET

# 12. Package outline



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## 13. Soldering



20 V, N-channel Trench MOSFET

# 14. Revision history

### **Table 8. Revision history**

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMV65UNEA v.1	20170317	Product data sheet	-	-

# 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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